

AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A method of forming an electronic device, said device comprising a FinFET (Fin Field Effect Transistor) containing a plurality of fins interconnected by fin connectors, said method comprising:

forming at least one localized stressor region within said device, said at least one localized stressor region being located on one of said fin connectors as a region of stressor material filling in an interior portion of said fin connector.

2. (Original) The method of claim 1, wherein said at least one localized stressor region comprises a first localized stressor region, said method further comprising:

forming a second localized stressor region within said device,
said first localized stressor region and said second localized stressor region causing a region therebetween to be stressed.

3. (Original) The method of claim 2, wherein said first localized stressor region and said second localized stressor region comprise a same type material.

4. (Original) The method of claim 3, wherein said same type material comprises one of a compressive stressor material and a tensile stressor material.

5. (Canceled)

6. (Currently amended) The method of claim 2, wherein said first and second localized stressor regions are formed on said fin connectors of said FinFET as regions of stressor material filling in interior portions of respective two fin connectors.

7-9. (Canceled)

10. (Original) The method of claim 4, wherein said same type material comprises a compressive material and primary charge carriers in said region being stressed comprise holes.

11. (Original) The method of claim 4, wherein said same type material comprises a tensile material and primary charge carriers in said region being stressed comprise electrons.

12. (Original) The method of claim 2, wherein said region being stressed causes a carrier mobility in said stressed region to be one of increased and decreased, relative to a carrier mobility in a region without said stress.

13. (Original) The method of claim 1, wherein said device comprises one of a plurality of devices in an electronic circuit, said method further comprising:

selectively providing a blocking mask over devices in said electronic circuit which are not to receive said at least one localized stressor region.

14. (Currently amended) A method of forming a stress region in an electronic device, said device comprising a FinFET (Fin Field Effect Transistor) containing a plurality of fins interconnected by fin connectors, said method comprising:

forming a first localized stressor region within said device on a first fin connector as comprising a first region of stressor material filling in an interior portion of said first fin connector; and

forming a second localized stressor region within said device on a second fin connector as comprising a second region of stressor material filling in an interior portion of said second fin connector.

said first localized stressor region and said second localized stressor region causing a region therebetween to be stressed.

15. (Original) The method of claim 14, wherein said region being stressed causes a carrier mobility in said stressed region to be one of increased and decreased, relative to a carrier mobility in a region without said stress.

16-22. (Canceled)

23. (Original) The method of claim 1, wherein at least one of said at least one localized stressor region interacts with a stressed region located outside said device.

24. (Original) The method of claim 1, wherein said at least one localized stressor region is used to generate one of a compression stress and a tensile stress.

25. (Original) The method of claim 1, wherein said at least one localized stressor region is located within said device to generate a stress that enhances a performance of said device.

26. (Original) The method of claim 25, wherein said performance enhancement comprises an increase in a carrier mobility.

27. (Original) The method of claim 25, wherein said performance enhancement comprises a decrease in a carrier mobility.

28. (Original) The method of claim 1, wherein said at least one localized stressor region is located to generate a stressed region in at least one of a direction parallel to a current flow and perpendicular to a current flow.

29. (Original) The method of claim 1, wherein said at least one localized stressor region is used to create a symmetrically stressed region.

30. (Original) The method of claim 1, wherein said at least one localized stressor region is used to create an asymmetrically stressed region.